**Product data sheet** 

# 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN0606-3 (SOT8001) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection up to 1.8 kV HBM
- Leadless ultra small and ultra thin SMD plastic package: 0.62 × 0.62 × 0.37 mm

### 3. Applications

- Relay driver
- High-speed line driver
- · Low-side load switch
- · Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

| Symbol            | Parameter                        | Conditions   |     | Min | Тур | Max | Unit |  |
|-------------------|----------------------------------|--|-----|-----|-----|-----|------|--|
| $V_{DS}$          | drain-source voltage             | T <sub>j</sub> = 25 °C   |     | -   | -   | 20  | V    |  |
| $V_{GS}$          | gate-source voltage              |  |     | -8  | -   | 8   | V    |  |
| I <sub>D</sub>    | drain current                    | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C                  | [1] | -   | -   | 1.2 | Α    |  |
| Static characte   | Static characteristics           |  |     |     |     |     |      |  |
| R <sub>DSon</sub> | drain-source on-state resistance | $V_{GS} = 4.5 \text{ V}; I_D = 0.7 \text{ A}; T_j = 25 \text{ °C}$ |     | -   | 260 | 310 | mΩ   |  |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



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# 5. Pinning information

**Table 2. Pinning information** 

| Pin | Symbol | Description | Simplified outline                       | Graphic symbol |
|-----|--------|-------------|--|----------------|
| 1   | G      | gate        | ПУ 7П                                    | D              |
| 2   | S      | source      |  |                |
| 3   | D      | drain       | Transparent top view DFN0606-3 (SOT8001) | S<br>017aaa255 |

# 6. Ordering information

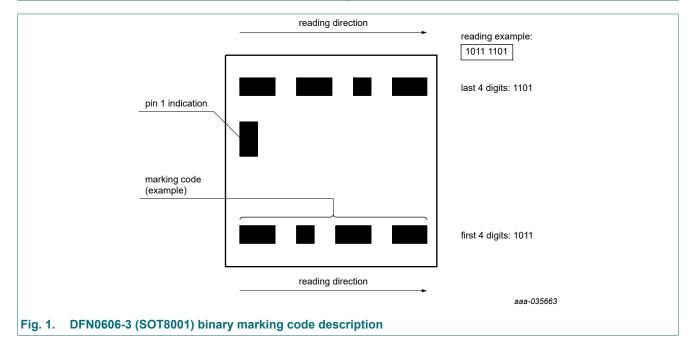
**Table 3. Ordering information** 

| Type number | Package |  |         |  |  |  |
|-------------|---------|--|---------|--|--|--|
|             | Name    | Description  | Version |  |  |  |
| PMH260UNE   |         | plastic, leadless ultra small package; 3 terminals; body 0.62 x 0.62 x 0.37 mm | SOT8001 |  |  |  |

# 7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMH260UNE   | 0001 0110    |



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### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions  |     | Min | Max  | Unit |
|------------------|-------------------------|---|-----|-----|------|------|
| V <sub>DS</sub>  | drain-source voltage    | T <sub>j</sub> = 25 °C                              |     | -   | 20   | V    |
| V <sub>GS</sub>  | gate-source voltage     |   |     | -8  | 8    | V    |
| I <sub>D</sub>   | drain current           | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C   | [1] | -   | 1.2  | Α    |
|                  |                         | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C  | [1] | -   | 0.73 | Α    |
| I <sub>DM</sub>  | peak drain current      | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$ |     | -   | 3    | Α    |
| P <sub>tot</sub> | total power dissipation | T <sub>amb</sub> = 25 °C                            | [2] | -   | 0.36 | W    |
|                  |                         |   | [1] | -   | 0.66 | W    |
|                  |                         | T <sub>sp</sub> = 25 °C                             |     | -   | 2.23 | W    |
| T <sub>j</sub>   | junction temperature    |   |     | -55 | 150  | °C   |
| T <sub>amb</sub> | ambient temperature     |   |     | -55 | 150  | °C   |
| T <sub>stg</sub> | storage temperature     |   |     | -65 | 150  | °C   |
| Source-draii     | n diode                 |   |     |     |      |      |
| Is               | source current          | T <sub>amb</sub> = 25 °C                            | [1] | -   | 0.6  | Α    |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

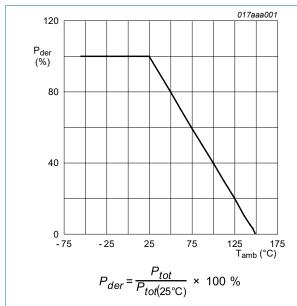


Fig. 2. Normalized total power dissipation as a function of ambient temperature

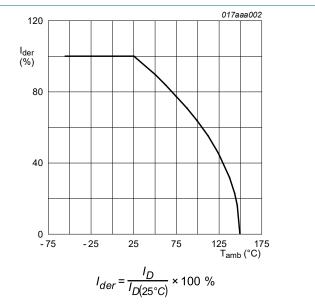


Fig. 3. Normalized continuous drain current as a function of ambient temperature

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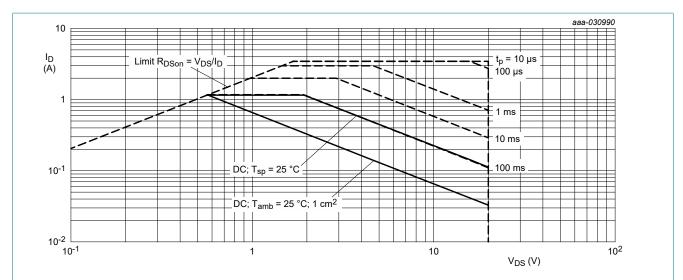


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol               | Parameter  | Conditions  |     | Min | Тур | Max | Unit |
|----------------------|--|-------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub> | thermal resistance from                          | in free air | [1] | -   | 287 | 344 | K/W  |
| junction to ambi     | junction to ambient                              |             | [2] | -   | 158 | 190 | K/W  |
| $R_{th(j-sp)}$       | thermal resistance from junction to solder point |             |     | -   | 47  | 56  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

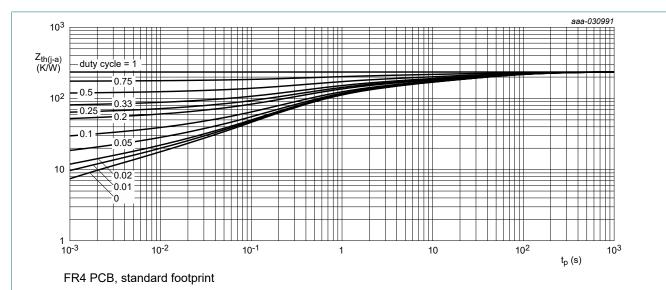


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

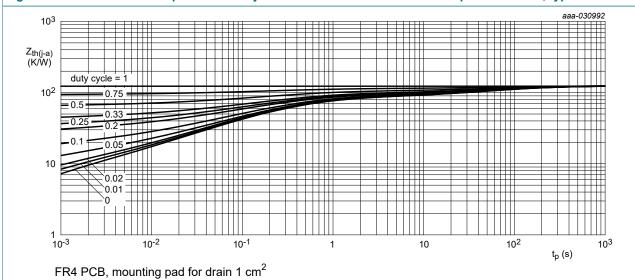


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

#### **Table 7. Characteristics**

| Symbol               | Parameter                         | Conditions   | Min      | Тур  | Max  | Unit |
|----------------------|-----------------------------------|--|----------|------|------|------|
| Static chara         | acteristics                       |  |          |      |      |      |
| V <sub>(BR)DSS</sub> | drain-source<br>breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$                               | 20       | -    | -    | V    |
| $V_{GSth}$           | gate-source threshold voltage     | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$                    | 0.45     | 0.7  | 0.95 | V    |
| I <sub>DSS</sub>     | drain leakage current             | V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C      | -        | -    | 1    | μΑ   |
|                      |                                   | V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C     | -        | -    | 20   | μΑ   |
| I <sub>GSS</sub>     | gate leakage current              | V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C       | -        | -    | 5    | μA   |
|                      |                                   | $V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$         | -        | -    | -5   | μΑ   |
|                      |                                   | $V_{GS} = 4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$  | -        | -    | 1    | μΑ   |
|                      |                                   | $V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$       | -        | -    | -1   | μΑ   |
|                      |                                   | $V_{GS} = 2.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$  | -        | -    | 0.1  | μΑ   |
|                      |                                   | $V_{GS} = -2.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | -        | -    | -0.1 | μΑ   |
| R <sub>DSon</sub>    | drain-source on-state             | $V_{GS} = 4.5 \text{ V}; I_D = 0.7 \text{ A}; T_j = 25 ^{\circ}\text{C}$   | -        | 260  | 310  | mΩ   |
|                      | resistance                        | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 0.7 A; T <sub>j</sub> = 150 °C   | -        | 410  | 490  | mΩ   |
|                      |                                   | $V_{GS} = 2.5 \text{ V}; I_D = 0.5 \text{ A}; T_j = 25 \text{ °C}$         | -        | 360  | 420  | mΩ   |
|                      |                                   | $V_{GS}$ = 1.8 V; $I_D$ = 0.05 A; $T_j$ = 25 °C                            | -        | 440  | 530  | mΩ   |
|                      |                                   | V <sub>GS</sub> = 1.5 V; I <sub>D</sub> = 0.01 A; T <sub>j</sub> = 25 °C   | -        | 530  | 920  | mΩ   |
| g <sub>fs</sub>      | forward transconductance          | $V_{DS} = 10 \text{ V}; I_D = 0.7 \text{ A}; T_j = 25 \text{ °C}$          | -        | 2.1  | -    | S    |
| R <sub>G</sub>       | gate resistance                   | f = 1 MHz  | -        | 11.2 | -    | Ω    |
| Dynamic ch           | naracteristics                    |  | <u>'</u> |      |      |      |
| Q <sub>G(tot)</sub>  | total gate charge                 | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 0.7 A; V <sub>GS</sub> = 4.5 V;   | -        | 0.63 | 0.95 | nC   |
| Q <sub>GS</sub>      | gate-source charge                | T <sub>j</sub> = 25 °C   | -        | 0.06 | -    | nC   |
| $Q_{GD}$             | gate-drain charge                 |  | -        | 0.18 | -    | nC   |
| C <sub>iss</sub>     | input capacitance                 | V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                  | -        | 41   | -    | pF   |
| C <sub>oss</sub>     | output capacitance                | T <sub>j</sub> = 25 °C   | -        | 10   | -    | pF   |
| C <sub>rss</sub>     | reverse transfer capacitance      |  | -        | 7    | -    | pF   |
| t <sub>d(on)</sub>   | turn-on delay time                | $V_{DS} = 10 \text{ V}; I_D = 0.7 \text{ A}; V_{GS} = 4.5 \text{ V};$      | -        | 1    | -    | ns   |
| t <sub>r</sub>       | rise time                         | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$                                       | -        | 2    | -    | ns   |
| t <sub>d(off)</sub>  | turn-off delay time               |  | -        | 4    | -    | ns   |
| t <sub>f</sub>       | fall time                         | 1  | -        | 2    | -    | ns   |
| Source-dra           | in diode                          |  |          |      |      |      |
| V <sub>SD</sub>      | source-drain voltage              | I <sub>S</sub> = 600 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C     | -        | 0.7  | 1.2  | V    |

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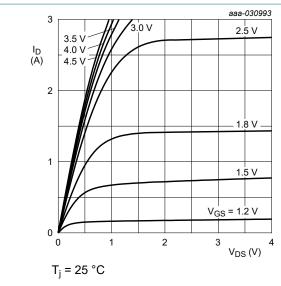


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

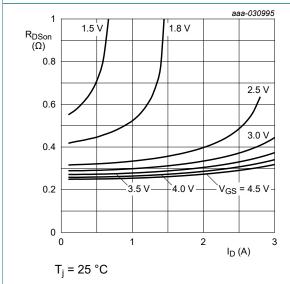


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

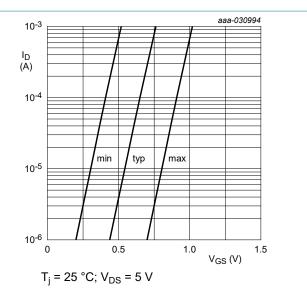


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

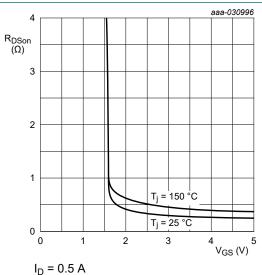


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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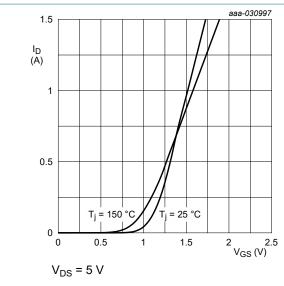


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

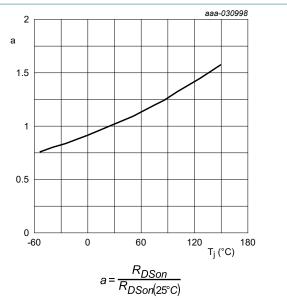


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

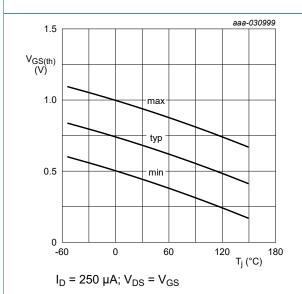


Fig. 13. Gate-source threshold voltage as a function of junction temperature

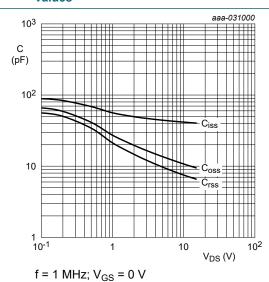


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### 20 V, N-channel Trench MOSFET

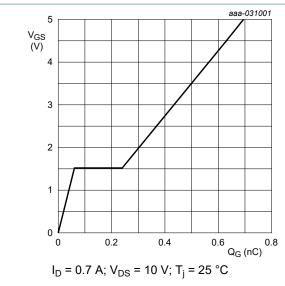


Fig. 15. Gate-source voltage as a function of gate charge; typical values

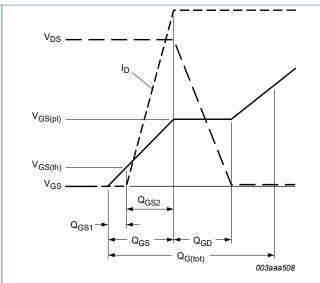


Fig. 16. Gate charge waveform definitions

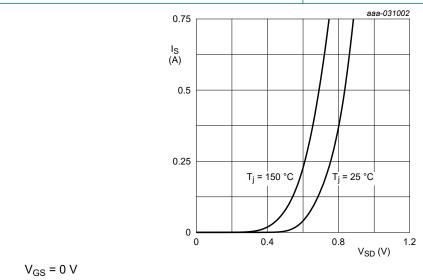
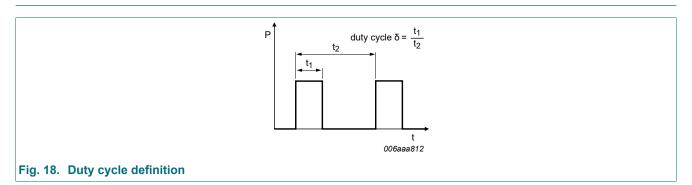


Fig. 17. Source current as a function of source-drain voltage; typical values

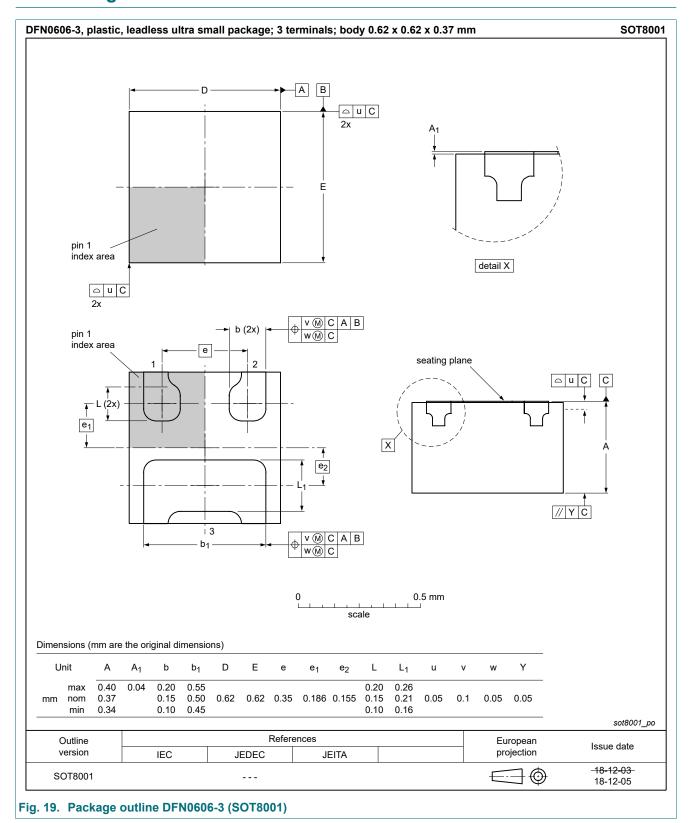
### 11. Test information



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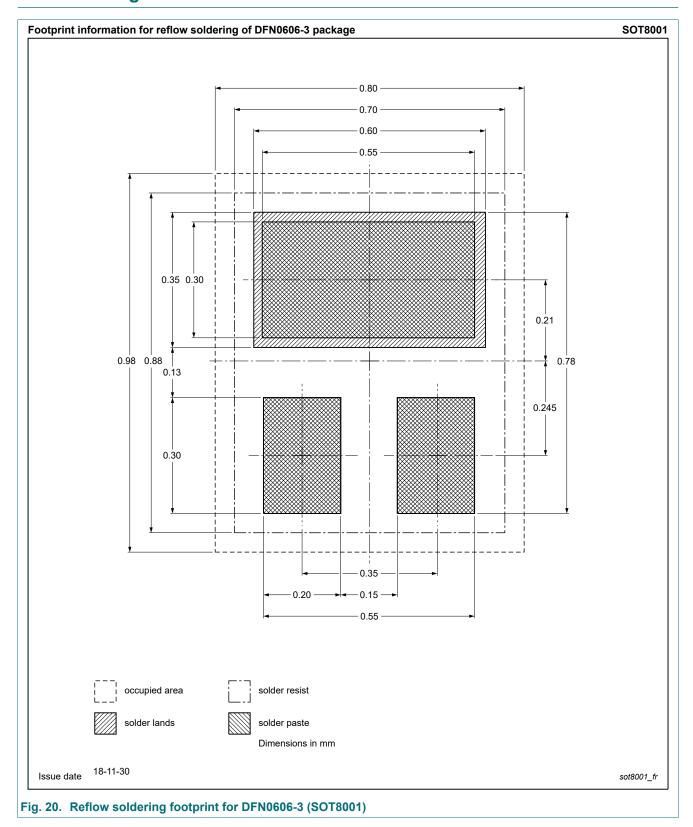
20 V, N-channel Trench MOSFET

# 12. Package outline



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# 13. Soldering



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# 14. Revision history

#### **Table 8. Revision history**

| Data sheet ID  | Release date                           | Data sheet status  | Change notice | Supersedes    |  |  |  |
|----------------|--|--------------------|---------------|---------------|--|--|--|
| PMH260UNE v.2  | 20230206                               | Product data sheet | -             | PMH260UNE v.1 |  |  |  |
| Modifications: | Fig. 1, clarifying the reading example |                    |               |               |  |  |  |
| PMH260UNE v.1  | 20200407                               | Product data sheet | -             | -             |  |  |  |

#### 20 V, N-channel Trench MOSFET

### 15. Legal information

#### **Data sheet status**

| Document status [1][2]         | Product<br>status [3] | Definition  |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet   | Development           | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification         | This document contains data from the preliminary specification.                       |
| Product [short]<br>data sheet  | Production            | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 6 February 2023

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